

SILICON PHOTODIODE

VTD34FSMH

PRELIMINARY ENGINEERING DATA SHEET

FEATURES

- Infrared transmiting package
- High sensitivity
- Low capacitance
- Fast response
- Low noise

PRODUCT DESCRIPTION

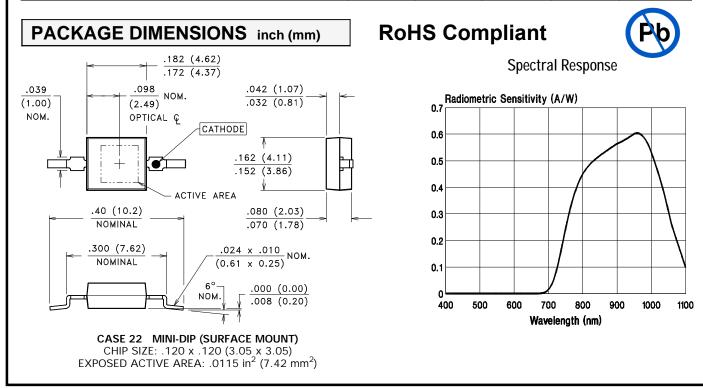
Planar silicon photodiode in an infrared transmitting, visible blocking molded plastic package.

This P on N photodiode is designed to provide excellent sensitivity at low levels of irradiance. Linearity is assured by its high shunt impedance and low series resistance.

Due to their low junction capacitance, these devices exhibit fast response, even with relatively high load resistances.

ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
RESPONSIVITY @ 0.5 mW/cm ² , 940 nm	Re	15			μA
DARK CURRENT @ V _R = 10 V	ID			30	nA
REVERSE BREAKDOWN VOLTAGE @ 100 μA	VBR	40			Volts
JUNCTION CAPACITANCE @ 1 MHz, V_R = 3 V	CJ			80	pF
RISE / FALL TIME @ 1 k Ω LOAD, V _R = 10 V, 833 nm	t _R / t _F		50		nsec
ACCEPTANCE ANGLE (BETWEEN 50% RESPONSE)	θ1/2		±50		Degrees



GENERAL CHARACTERISTICS							
PARAMETER	SYMBOL	TYPICAL RATING	UNITS				
OPEN CIRCUIT VOLTAGE @ 0.5 mW/cm ² , 940 nm	V _{OC}	350	mV				
PEAK SPECTRAL RESPONSE @ 25°C	λpk	940	nm				
SPECTRAL APPLICATION RANGE	λrange	725 - 1150	nm				
RADIOMETRIC SENSITIVITY @ PEAK, 25°C	Srpk	0.60	A / W				
NOISE EQUIVALENT POWER	NEP	4.8 x 10 ⁻¹⁴	W /√Hz				
SPECIFIC DETECTIVITY	D*	5.7 x 10 ¹²	$cm\sqrt{Hz}$ / W				
TEMPERATURE COEFFICIENT OPEN CIRCUIT VOLTAGE @ 2850 K SOURCE DARK CURRENT	TC Voc TC ID	- 2.0 +15.0	mV / °C % / °C				
TEMPERATURE RANGE OPERATING STORAGE	To Ts	- 20 to +80 - 20 to +80	°C °C				



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